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AMENDMENTS TO THE CLAIMS

1. (Currently amended) A method of cleaning a chemical vapor deposition (CVD) reaction chamber with cleaning gas provided through a remote plasma discharge chamber, comprising:

dissociating cleaning gas within the remote plasma discharge chamber, wherein said dissociated cleaning gas is exposed to an anodized aluminum alloy wall of the remote plasma discharge chamber;

supplying activated species from the remote plasma discharge chamber to the reaction chamber through a piping, ~~wherein a surface of the piping that is exposed to the activated species is a fluorine passivated surface;~~

opening a valve on the piping after conducting a CVD reaction and prior to supplying activated species, wherein opening a valve comprises withdrawing a valve body completely from a path to form an opening substantially as wide as internal surfaces of the piping; and

removing adhered deposits from CVD reactions on a wall of the reaction chamber.

2-10. (Cancelled).

11. (Previously presented) The method of Claim 1, further comprising closing the valve after removing the adhered deposits.

12-39. (Cancelled).

40. (New) The method of Claim 1, wherein removing adhered deposits comprises removing adhered silicon nitride deposits.

41. (New) The method of Claim 1, wherein the cleaning gas comprises fluorine-containing gas and the activated species comprises fluorine active species.

42. (New) The method of Claim 1, wherein the applied energy has a frequency between about 300 kHz and 500 kHz.

43. (New) The method of Claim 1, wherein supplying activated species comprises flowing NF_3 through the remote plasma discharge chamber at a rate between about 0.5 slm and 1.5 slm.